

Silicon NPN Power Transistors

2SC2534

DESCRIPTION

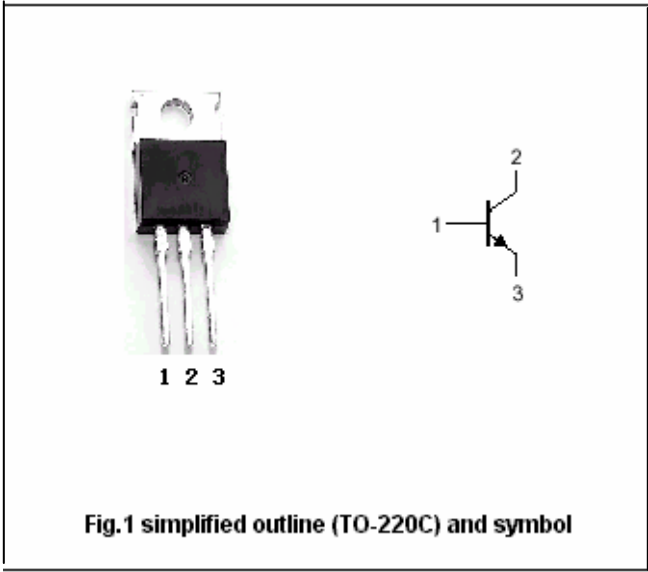
- With TO-220C package
- High collector breakdown voltage
: $V_{CEO}=400V(\text{Min})$
- Excellent switching time
: $t_r=1.0\mu s(\text{Max.})$
: $t_f=1.0\mu s(\text{Max.})$

APPLICATIONS

- High speed high voltage switching applications
- Switching regulator applications
- High speed DC-DC converter applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		2	A
I_B	Base current		0.5	A
P_C	Collector dissipation	$T_a=25^\circ\text{C}$	1.5	W
		$T_C=25^\circ\text{C}$	20	
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=10mA$; $I_B=0$	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA$; $I_E=0$	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=0.5A$; $I_B=50mA$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=0.5A$; $I_B=50mA$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V$; $I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V$; $I_C=0$			1	mA
h_{FE-1}	DC current gain	$I_C=0.1A$; $V_{CE}=5V$	20			
h_{FE-2}	DC current gain	$I_C=0.5A$; $V_{CE}=5V$	20			

Switching times

t_r	Rise time	$V_{CC}=200V$; $I_{B1}=-I_{B2}=50mA$; $R_L=400\Omega$ Duty cycle $\leq 1\%$			1.0	μs
t_{stg}	Storage time				2.5	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

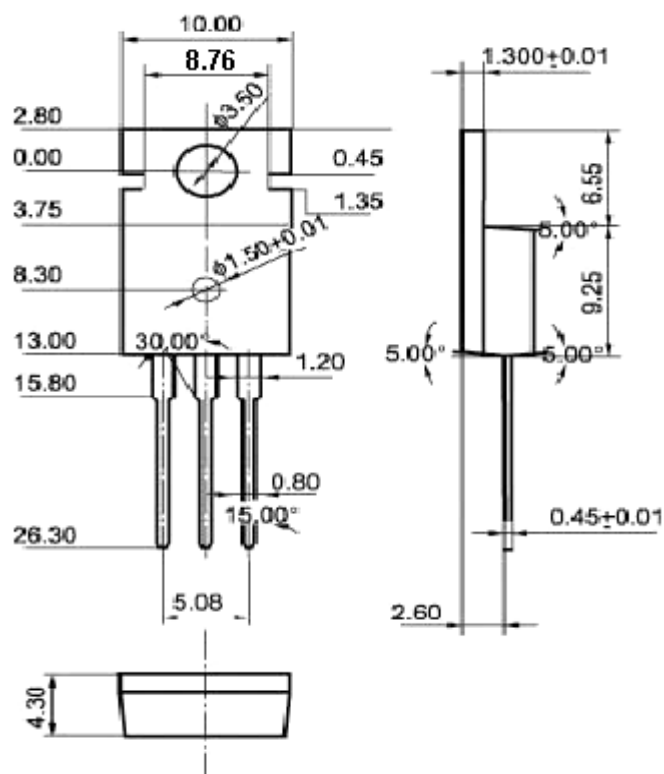


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)

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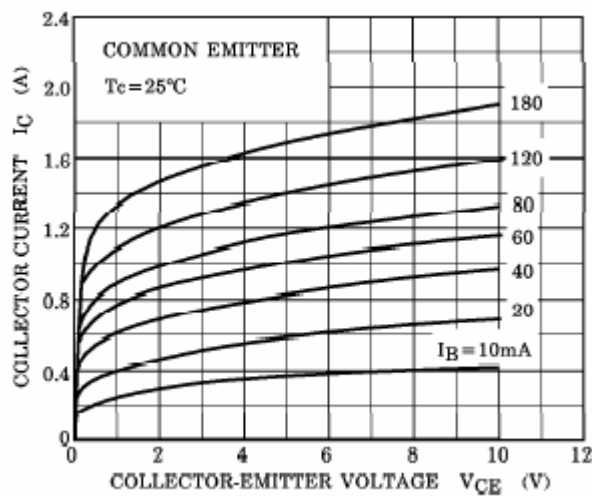


Fig.3 Static Characteristic

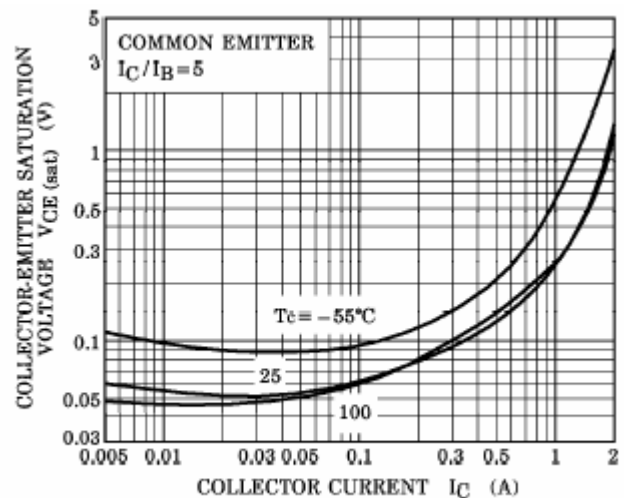


Fig.4 Collector-Emitter Saturation Voltage

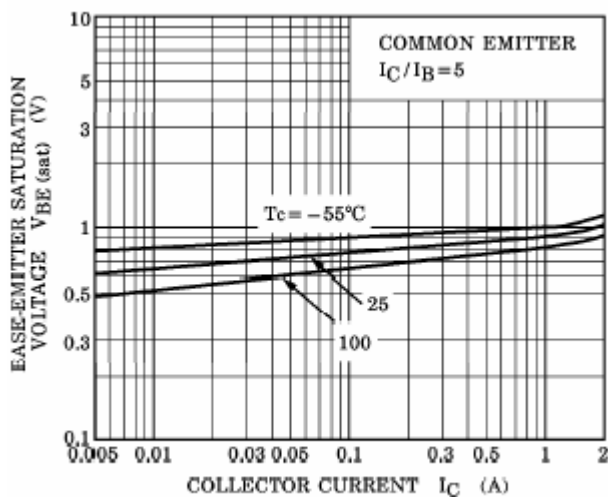


Fig.5 Base-Emitter Saturation Voltage

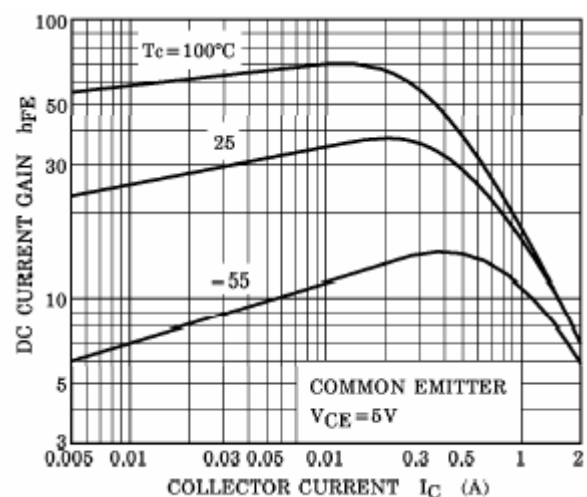


Fig.6 DC current Gain

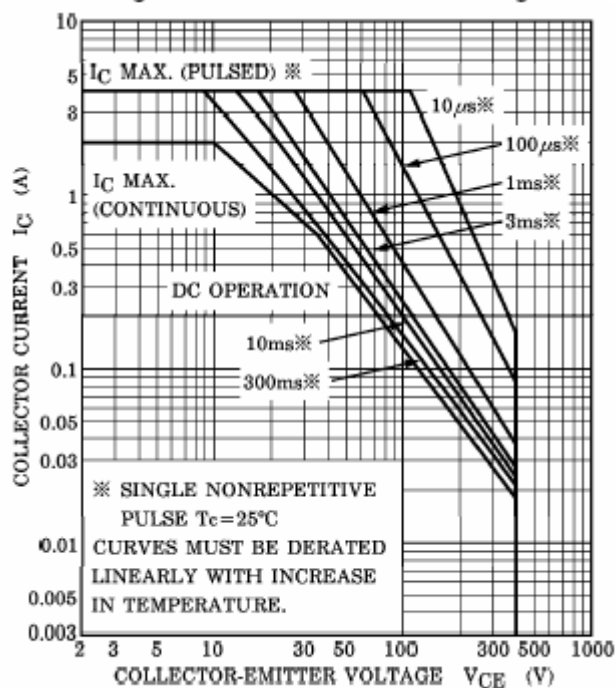


Fig.7 Safe Operating Area